

LC89517K

Built-in Subcode Interface CD-ROM/CD-I Error Correction LSI

Preliminary

Overview

The LC89517K is a CD-ROM/CD-I error correction LSI that integrates the functions provided by the improved version of the LC89515 and a sub-code function in a single chip. The improved version of the LC89515 additionally supports double speed operation.

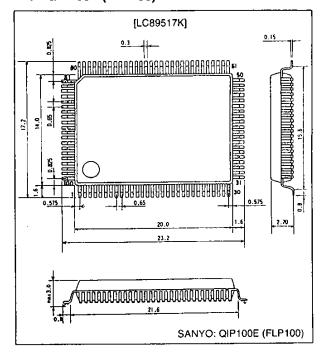
Features

- Support for double speed operation (selectable by setting an internal register) at an operating frequency of 16.9344 MHz
- Built-in 12-byte FIFO for transfers from the system microcontroller to the host computer
- Built-in 12-byte FIFO for transfers from the host computer to the system microcontroller
- Direct connection to the LC8955 (an ADPCM decoder LSI) and the LC8953 (a 68000 CPU peripheral interface LSI)
- Sub-code data can be written to buffer RAM simply by connecting the CD DSP sub-code pin. This allows the system microcontroller to read the sub-code values.
- The system microcontroller can access buffer RAM through the LC89517K.
- Pseudo-SRAM support (An interface circuit is built in.)

Package Dimensions

unit: mm

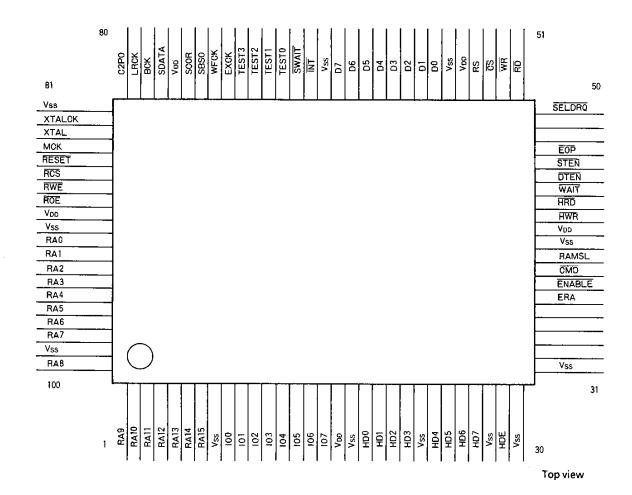
3151-QIP100E (FLP100)



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Pin Assignment



PIn Functions

Type: I: Input pin, O: Output pin, B: Bidirectional pin, P: Power supply pin, NC: Unconnected pin

Pin No.	Pin	Туре	Type: I: Input pin, O: Output pin, B: Bidirectional pin, P: Power supply pin, NC: Unconnected pin Function
1	RA9	0	
2	RA10	 	· · · · · ·
3	RA11	 	
4	RA12	 	Data buffer RAM address signal outputs
5	RA13	10	
6	RA14	10	
7	RA15	1 0	
8	V _{SS}	P	
9	100	В	Data buffer RAM data signals
10	IO1	В	These pins have built-in pull-up resistors.
11	102	В	
12	103	В	
13	104	Т <u>Б</u>	
14	IO5	В	
15	106	В	Data buffer RAM data signals
16	107	В	These pins have built-in pull-up resistors.
17	V _{DD}	P	Triade principals and property.
18	V _{SS}	P	
19	HD0	В	
20	HD1	В	Heat data alamaia
21	HD2	B	Host data signals These pins have built-in pull-up resistors.
22	HD3	- B	These pile have balk in pair up resisters.
23	V _{SS}	P	
24	HD4	B	
25	HD5	В	
26	HD6	B	Host data signals These pins have built-in pull-up resistors
27	HD7	8	These pine nave sent in pair ap resistant
28		P	
29	V _{SS} HDE	0	Heat against the county (Connect to M. Hungard)
30		P	Host erasure flag output (Connect to V _{DD} if unused.)
31	V _{SS}	P	
32	V _{SS}	NC NC	
33		NC NC	
34		NC NC	
35	EDA	NC P	Data huffer DAM argue for sized (Consents VIII)
36	ERA	В	Data buffer RAM erasure flag signal (Connect to V _{SS} if unused.)
37	ENABLE	+ !	Chip select signal input (from host computer)
38	CMD	 	Host command/data selection signal
39	RAMSL	1 1	DRAM/SRAM switch
40	V _{SS}	P	
41	V _{DD}	P	
42	HWR	1	Host data write signal input
43	HRD	1	Host data read signal input
44	WAIT	0	Walt signal output (to host). This pin can be switched to function as the DRQ signal.
45	DTEN	0	Data enable signal output
46	STEN	0	Status enable signal output
47	EOP	0	End of process signal output. Used during DMA transfers.
48	<u> </u>	NC	
49		NC	
50	SELDRQ	!!	Selects the mode for data transfers to the host.

Continued on next page.

LC89517K

Continued from preceding page.

ST	Pin No.	Pin	Туре	Function					
Section									
S3			 						
Section Sect									
55	-								
55									
S7 DO									
Se	$\overline{}$			· · · · · · · · · · · · · · · · · · ·					
S9									
Microcontroller data signals. These pins have built-in pull-up resistors.			ļ						
61				Missessantselles data sinnula					
Columbia Columbia	\vdash								
B	$\overline{}$			1					
64									
65				•					
Interrupt request signal output (to the microcontroller)									
SWAIT	·			Interrupt request signal output (to the microcontroller)					
Best Test				This pin is an open drain output with a built-in pull-up resistor.					
FeST1			ļ	System microcontroller wait signal					
Test									
71 TEST3	69			Test inputs. These pins should be tied low during normal operation					
72	70	TEST2	1	Total in pale. These pins should be field low during hornal epotation.					
73 WFCK									
74			0						
74	73	WFCK	1	Sub-mde I/O					
76	74	SBSO	1	our code #0					
77 SDATA I Serial data input 78 BCK I Serial data input clock 79 LRCK I 44.1 kHz strobe signal input 80 C2PO I C2 pointer input 81 Vss P 82 XTALCK I Crystal oscillator output 83 XTAL O Crystal oscillator output 84 MCK O Outputs the XTALCK input signal divided by 2. 85 RESET I Chip select signal input 86 RCS O RAM chip select 87 RWE O RAM data write signal 88 ROE O RAM data read signal 89 V _{DD} P 90 Vss P 91 RAO O 92 RA1 O 93 RA2 O 94 RA3 O 95 RA4 O 96 RA5 O <	.75		t						
78			Ρ						
79									
80	78	BCK	1	Serial data input clock					
81	79		1	44.1 kHz strobe signal input					
82 XTALCK I Crystal oscillator input 83 XTAL O Crystal oscillator output 84 MCK O Outputs the XTALCK input signal divided by 2. 85 RESET I Chip select signal input 86 RCS O RAM chip select 87 RWE O RAM data write signal 88 ROE O RAM data read signal 89 V _{DD} P 90 V _{SS} P 91 RAO O 92 RA1 O 93 RA2 O 94 RA3 O 95 RA4 O 96 RA5 O 97 RA6 O 98 RA7 O 99 V _{SS} P	80			C2 pointer input					
83 XTAL O Crystal oscillator output 84 MCK O Outputs the XTALCK input signal divided by 2. 85 RESET I Chip select signal input 86 RCS O RAM chip select 87 RWE O RAM data write signal 88 ROE O RAM data read signal 89 VpD P 90 Vss P 91 RAO O 92 RA1 O 93 RA2 O 94 RA3 O 95 RA4 O 96 RA5 O 97 RA6 O 98 RA7 O 99 Vss P	81	V _{SS}	P						
84 MCK O Outputs the XTALCK input signal divided by 2. 85 RESET I Chip select signal input 86 RCS O RAM chip select 87 RWE O RAM data write signal 88 ROE O RAM data read signal 89 V _{DD} P 90 V _{SS} P 91 RAO O 92 RA1 O 93 RA2 O 94 RA3 O 95 RA4 O 96 RA5 O 97 RA6 O 98 RA7 O 99 V _{SS} P	82	XTALCK	ı	Crystal oscillator input					
B5 RESET Chip select signal input	83	XTAL	0	Crystal oscillator output					
86 RCS O RAM chip select 87 RWE O RAM data write signal 88 ROE O RAM data read signal 89 V _{DD} P 90 V _{SS} P 91 RA0 O 92 RA1 O 93 RA2 O 94 RA3 O 95 RA4 O 96 RA5 O 97 RA6 O 98 RA7 O 99 V _{SS} P	84	MCK	0	Outputs the XTALCK input signal divided by 2.					
87 RWE O RAM data write signal 88 ROE O PAM data read signal 89 V _{DD} P 90 V _{SS} P 91 RA0 O 92 RA1 O 93 RA2 O 94 RA3 O 95 RA4 O 96 RA5 O 97 RA6 O 98 RA7 O 99 V _{SS} P	85			Chip select signal input					
88 ROE O RAM data read signal 89 V _{DD} P 90 V _{SS} P 91 RA0 O 92 RA1 O 93 RA2 O 94 RA3 O 95 RA4 O 96 RA5 O 97 RA6 O 98 RA7 O 99 V _{SS} P	86	RCS	0	RAM chip select					
89 V _{DD} P 90 V _{SS} P 91 RA0 O 92 RA1 O 93 RA2 O 94 RA3 O 95 RA4 O 96 RA5 O 97 RA6 O 98 RA7 O 99 V _{SS} P	87		0						
90	88		0	RAM data read signal					
90	89	V _{DD}	Р						
91 RA0 O 92 RA1 O 93 RA2 O 94 RA3 O 95 RA4 O 96 RA5 O 97 RA6 O 98 RA7 O 99 VSS P	90		Р						
93 RA2 O 94 RA3 O 95 RA4 O 96 RA5 O 97 RA6 O 98 RA7 O 99 VSS P	91	RA0	0						
94 RA3 O 95 RA4 O 96 RA5 O 97 RA6 O 98 RA7 O 99 V _{SS} P	92	RA1	0						
95 RA4 O Data buffer RAM address signal outputs 96 RA5 O 97 RA6 O 98 RA7 O 99 V _{SS} P	93	RA2	0						
95 RA4 O 96 RA5 O 97 RA6 O 98 RA7 O 99 V _{SS} P	94	RA3	0	Data huffer RAM address signal outputs					
97 RA6 O 98 RA7 O 99 V _{SS} P	95	RA4	0	Data buffer RAM address signal outputs					
98 RA7 O 99 V _{SS} P	96	RA5	0						
99 V _{SS} P	97	RA6	0						
30	98	RA7	0						
	99	V _{SS}	P						
TOU TIME O Data buller HAM address signal output	100	RA8	0	Data buffer RAM address signal output					

Specifications

Absolute Maximum Ratings at $V_{SS} = 0 \text{ V}$

Parameter	Symbol	Conditions	Ratings	Unit
Maximum supply voltage	V _{DD} max	Ta = 25°C	-0.3 to +7.0	V
I/O voltage	V _I , V _O	Ta = 25°C	-0.3 to V _{DD} + 0.3	٧
Allowable power dissipation	Pd max	Ta≤70°C	350	mW
Operating temperature	Topr		-30 to +70	°C
Storage temperature	Tstg		-55 to +125	°C
Soldering temperature		10 seconds	260	°C

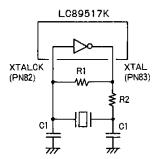
Allowable Operating Ranges at $Ta = -30 \text{ to } +70^{\circ}\text{C}, V_{SS} = 0 \text{ V}$

Parameter	Symbol	Conditions	min	typ	max	Unit
Supply voltage	V _{DD}		3.5	5.0	5.5	٧
Input voltage range	V _{IN}		0		V _{DD}	٧

DC Characteristics at Ta = -30 to +70°C, V_{SS} = 0 V, V_{DD} = 3.5 to 5.5 V

Parameter	Symbol	Conditions	min	typ	max	Unit
Input high level voltage	V _{IH1}	V _{IH1}				V
Input low level voltage V _{IL1}		All input pins other than (1) and XTALCK			0.8	V
Input high level voltage	V _{IH2}	RESET, all bus pins (HRD, HWR, ENABLE, CMD, RD,	2.5			V
Input low level voltage	V _{IL2}	CS, WR, WFCK, SBSO, SCOR) (1)			0.6	V
Output high level voltage	V _{OH1}	I _{OH1} = -2 mA: All output pins (including bus pins) other than (2) and XTALCK	2.4			٧
Output low level voltage	V _{OL1}	f _{OL1} = 2 mA: All output pins (including bus pins) other than (2) and XTALCK			0.4	٧
Output low level voltage	V _{OL2}	I _{OL2} = 2 mA: INT (open drain circuit with pull-up resistor) (2)			0.4	٧
Output high level voltage	V _{OH3}	I _{OH3} = -6 mA: HD0 to HD7	2.4			V
Output low level voltage	V _{OL3}	I _{OL3} = 6 mA: HD0 to HD7			0.4	V
Input leakage current	IL.	V _I = V _{SS} , V _{DD} : All input pins	-25		+25	μА
Pull-up resistance	R _{UP}	All bus pins, INT	10	20	40	kΩ

Sample Recommended Oscillator Circuit



R1 = 120 k Ω R2 = 47 Ω C1 = 30 pF Crystal oscillator frequency = 16.9344 MHz